METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

There is provided a technique that includes: (a) forming an oxide layer containing a predetermined element on a first film formed on a substrate by supplying a precursor gas containing the predetermined element to the substrate such that hydroxyl group terminations are formed on a surface of the oxide layer and a density of the hydroxyl group terminations on the oxide layer is higher than a density of hydroxyl group terminations on a surface of the first film before (a); and (b) hydrophobizing the surface of the oxide layer by supplying a modifying gas containing a hydrocarbon group to the substrate.

FIG. 4